HybridPACK™ Drive module with CoolSiC™ Automotive MOSFET

Features

- Electrical features
  - V_{DSS} = 1200 V
  - $I_{D,nom}$ = 200 A
  - New semiconductor material - silicon carbide
  - Blocking voltage 1200 V
  - Low $R_{DS,on}$
  - Low switching losses
  - Low Q_g and C_{rss}
  - $T_{vj,op}$ = 150°C
  - Low inductive design <10 nH
- Mechanical features
  - 4.2 kV DC 1 second insulation
  - High creepage and clearance distances
  - Compact design
  - High power density
  - Direct-cooled PinFin base plate
  - High-performance Si3N4 ceramic
  - Guiding elements for PCB and cooler assembly
  - Integrated NTC temperature sensor
  - PressFIT contact technology
  - RoHS compliant
  - UL 94 V0 module frame

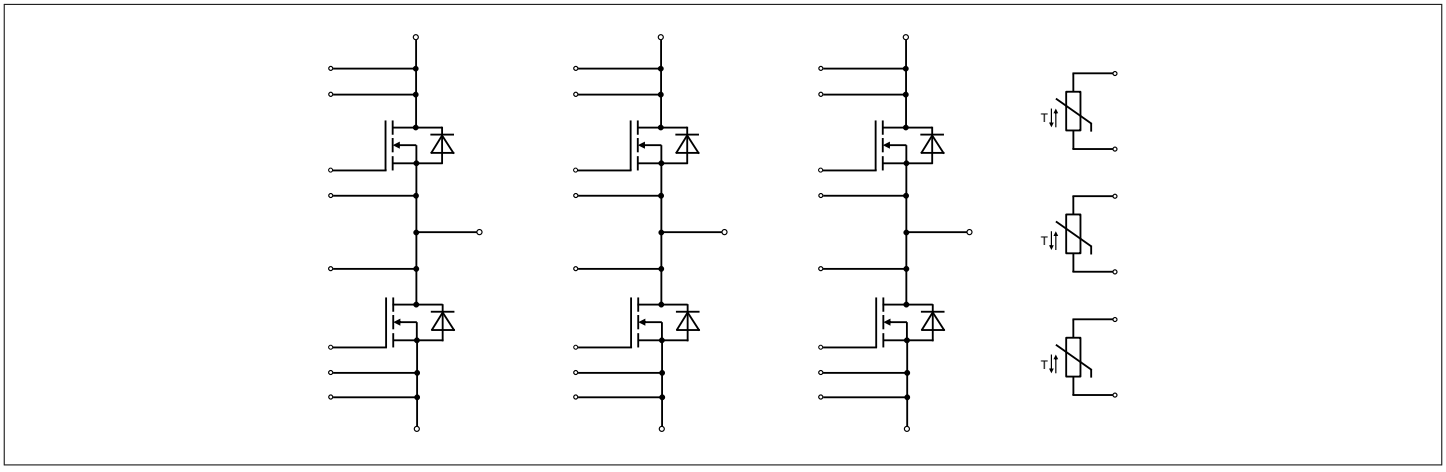
Potential applications

- Automotive applications
- (Hybrid) electrical vehicles (H)EV
- Motor drives
- Commercial agriculture vehicles

Product validation

- Qualified according to AQG 324, release no.: 03.1/2021

Description



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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 0 Hz, t = 1 sec	4.20	kV
Material of module baseplate			Cu+Ni[1)]	
Internal isolation		basic insulation (class 1, IEC 61140)	Si3N4	
Creepage distance	d_{creep}	terminal to heatsink	9.0	mm
Creepage distance	d_{creep}	terminal to terminal	9.0	mm
Clearance	d_{clear}	terminal to heatsink	4.5	mm
Clearance	d_{clear}	terminal to terminal	4.5	mm
Comparative tracking index	*CTI*		> 200	

1) Ni plated Cu baseplate.

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Maximum RMS module terminal current	$I_{t,rms}$	$T_{terminal}$ = 105 °C, T_f = 75 °C	550	A

Table 3 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Pressure drop in cooling circuit	Δp	$\Delta V/\Delta t$ = 10 dm³/min, 50% water/ 50% ethylenglycol, T_f = 60 °C		64[1)]		mbar
Maximum pressure in cooling circuit	p	$T_{baseplate}$ < 40 °C (relative pressure)			2.5	bar
		$T_{baseplate}$ ≥ 40 °C (relative pressure)			2.0	
Stray inductance module	$L_{s,DS}$			8.5		nH
Module lead resistance, terminals - chip	$R_{DD'+SS'}$	T_f = 25 °C, per switch		0.75		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for module mounting	M	Screw M4 baseplate to heatsink	1.8	2.0	2.2	Nm
Weight	G			720		g

1) Cooler design and flow direction according to application note AN-HPD-ASSEMBLY.

2 MOSFET

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		T_{vj} = 25 °C	1200	V
DC drain current	$I_{D,nom}$	V_{GS} = 15 V, T_f = 60 °C	$T_{vj,max}$ = 175 °C	200	A
Pulsed drain current	$I_{D,pulse}$	verified by design, t_p limited by T_{vjmax}		400	A
Gate-source voltage	V_{GSS}			-10/20	V

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS,on}$	I_D = 200 A, V_{GS} = 15 V	T_{vj} = 25 °C		5.50	7.35	mΩ
			T_{vj} = 125 °C		8.00		
			T_{vj} = 150 °C		9.10		
Gate threshold voltage	$V_{GS,th}$	I_D = 120 mA, V_{GS} = V_{DS}, (tested after 1ms pulse at V_{GS} = +20 V)	T_{vj} = 25 °C	3.25	4.50	5.55	V
Total gate charge	Q_G	V_{DS} = 600 V, V_{GS} = -5/15 V			0.66		µC
Internal gate resistor	$R_{G,int}$		T_{vj} = 25 °C		0.45		Ω
Input capacitance	C_{iss}	f = 1 MHz, V_{DS} = 600 V, V_{GS} = 0 V	T_{vj} = 25 °C		21.3		nF
Output capacitance	C_{oss}	f = 1 MHz, V_{DS} = 600 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.93		nF
Reverse transfer capacitance	C_{rss}	f = 1 MHz, V_{DS} = 600 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.09		nF
C_{OSS} stored energy	E_{oss}	V_{DS} = 600 V, V_{GS} = -5/15 V	T_{vj} = 25 °C		219		µJ
Drain-source leakage current	I_{DSX}	V_{GS} = -5 V, V_{DSS} = 1200 V	T_{vj} = 25 °C			100	µA
Gate-source leakage current	I_{GSS}	V_{GS} = 20 V, V_{DS} = 0 V	T_{vj} = 25 °C			400	nA
Turn-on delay time, inductive load	$t_{d,on}$	I_D = 200 A, $R_{G,on}$ = 5.1 Ω, V_{GS} = -5/15 V, V_{DS} = 600 V	T_{vj} = 25 °C		52		ns
			T_{vj} = 125 °C		45		
			T_{vj} = 150 °C		44		
Rise time (inductive load)	t_r	I_D = 200 A, $R_{G,on}$ = 5.1 Ω, V_{GS} = -5/15 V, V_{DS} = 600 V	T_{vj} = 25 °C		44		ns
			T_{vj} = 125 °C		40		
			T_{vj} = 150 °C		39		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off delay time, inductive load	$t_{d,off}$	I_D = 200 A, $R_{G,off}$ = 5.1 Ω, V_{GS} = -5/15 V, V_{DS} = 600 V	T_{vj} = 25 °C		142		ns
			T_{vj} = 125 °C		153		
			T_{vj} = 150 °C		156		
Fall time (inductive load)	t_f	I_D = 200 A, $R_{G,off}$ = 5.1 Ω, V_{GS} = -5/15 V, V_{DS} = 600 V	T_{vj} = 25 °C		52		ns
			T_{vj} = 125 °C		53		
			T_{vj} = 150 °C		53		
Turn-on energy loss per pulse	E_{on}	I_D = 200 A, $R_{G,on}$ = 5.1 Ω, V_{GS} = -5/15 V, V_{DS} = 600 V, L_σ = 20 nH	T_{vj} = 25 °C		6.04		mJ
			T_{vj} = 125 °C		6.66		
			T_{vj} = 150 °C, di/dt = 4.5 kA/µs		6.83		
Turn-off energy loss per pulse	E_{off}	I_D = 200 A, $R_{G,off}$ = 5.1 Ω, V_{GS} = -5/15 V, V_{DS} = 600 V, L_σ = 20 nH	T_{vj} = 25 °C		4.27		mJ
			T_{vj} = 125 °C		4.41		
			T_{vj} = 150 °C, du/dt = 12.4 kV/µs		4.51		
Short circuit data	I_{SC}	V_{DD} = 800 V, V_{GS} = -5/15 V, $R_{G,on}$ = 5.1 Ω, $R_{G,off}$ = 5.1 Ω, V_{DSmax} = V_{DSS}-L_{sDS}·di/dt	t_{SC} ≤ 3 µs, T_{vj} = 25 °C		2730		A
			t_{SC} ≤ 3 µs, T_{vj} = 150 °C		2480		
Thermal resistance, junction to cooling fluid	$R_{th,j-f}$	per MOSFET, T_f = 60 °C, $\Delta V/\Delta t$ = 10 dm³/min, 50% water/ 50% ethylenglycol			0.15	0.18[1)]	K/W
Temperature under switching conditions	$T_{vj,op}$			-40		150	°C

1) EoL criteria see AQG324, verified by characterization with 4.5 sigma. Cooler design and flow direction according to application note AN-HPDPERF-ASSEMBLY

3 Body diode

Table 6 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	$I_{F,S}$	$T_{vj,max}$ = 175 °C, V_{GS} = -5 V	T_f = 60 °C	110	A
Pulsed body diode current	$I_{F,S,pulse}$	verified by design, t_p limited by T_{vjmax}		400	A

Table 7 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	$V_{F,SD}$	$I_{F,S}$ = 200 A, V_{GS} = -5 V	T_{vj} = 25 °C		4.42	6.15	V
			T_{vj} = 125 °C		4.22		
			T_{vj} = 150 °C		4.16		
Peak reverse recovery current	I_{rrm}	$I_{F,S}$ = 200 A, V_{GS} = -5 V, $V_{R,DS}$ = 600 V	T_{vj} = 25 °C		87		A
			T_{vj} = 125 °C		165		
			T_{vj} = 150 °C		187		
Recovered charge	Q_{rr}	$I_{F,S}$ = 200 A, V_{GS} = -5 V, $V_{R,DS}$ = 600 V	T_{vj} = 25 °C		3.67		µC
			T_{vj} = 125 °C		6.81		
			T_{vj} = 150 °C		8.28		
Reverse recovery energy	E_{rec}	$I_{F,S}$ = 200 A, V_{GS} = -5 V, $V_{R,DS}$ = 600 V	T_{vj} = 25 °C, $-di/dt$ = 1.0 kA/µs		0.5		mJ
			T_{vj} = 125 °C, $-di/dt$ = 1.0 kA/µs		1.1		
			T_{vj} = 150 °C, $-di/dt$ = 1.0 kA/µs		1.4		

4 NTC-Thermistor

Table 8 Characteristic values

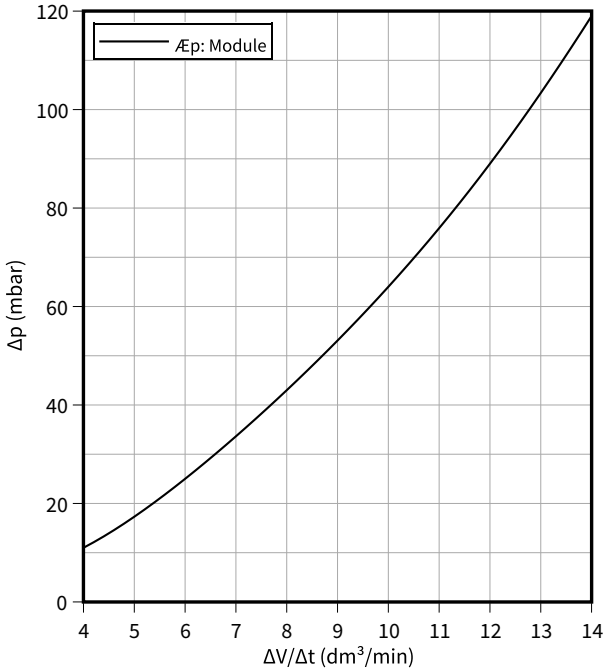
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	T_{NTC} = 25 °C		5		kΩ
Deviation of R_{100}	$\Delta R/R$	T_{NTC} = 100 °C, R_{100} = 493 Ω	-5		5	%
Power dissipation	P_{25}	T_{NTC} = 25 °C			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2-1/(298{,}15\ K))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2-1/(298{,}15\ K))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2-1/(298{,}15\ K))]$		3433		K

5 Characteristics diagrams

Pressure drop in cooling circuit, Package

$\Delta p = f(\Delta V/\Delta t)$

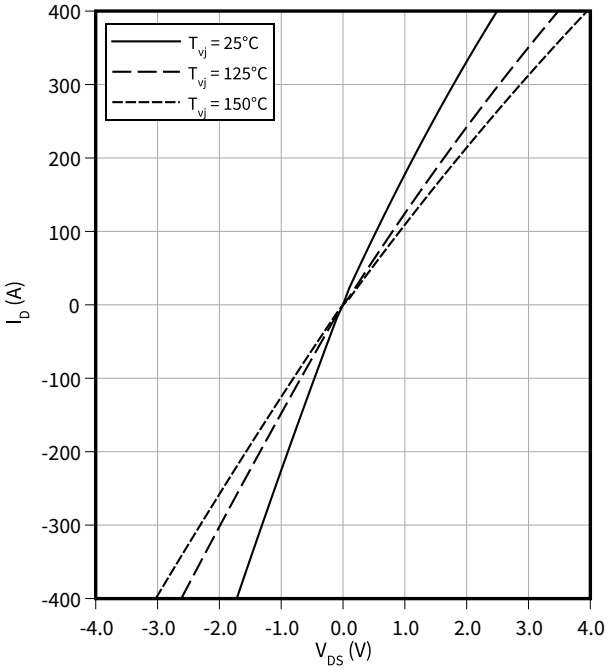
T_f = 60 °C, fluid = 50% water/ 50% ethylenglycol



Output characteristic (typical), MOSFET

$I_D = f(V_{DS})$

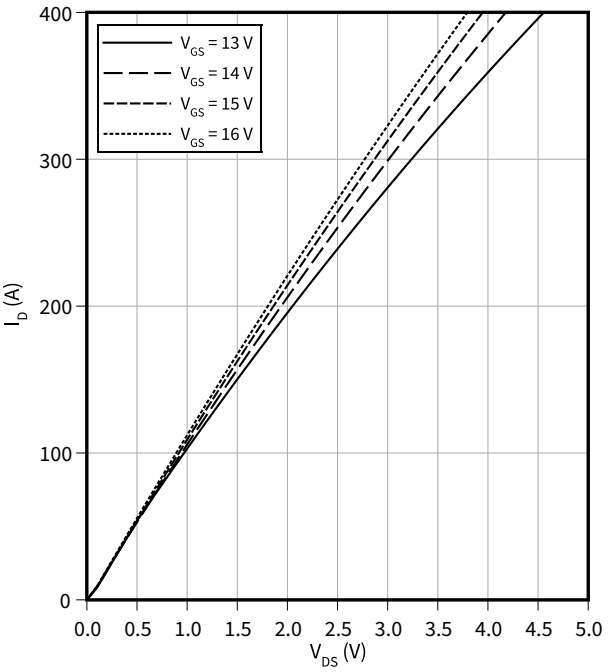
V_{GS} = 15 V



Output characteristic (typical), MOSFET

$I_D = f(V_{DS})$

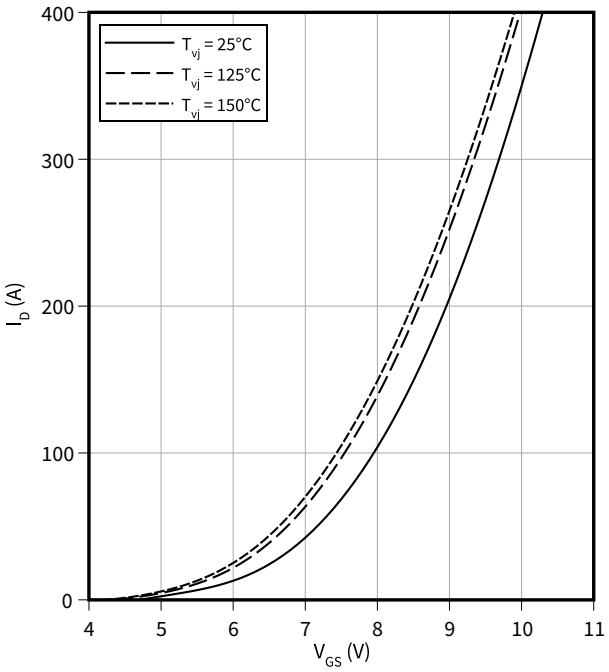
T_{vj} = 125 °C



Transfer characteristic (typical), MOSFET

$I_D = f(V_{GS})$

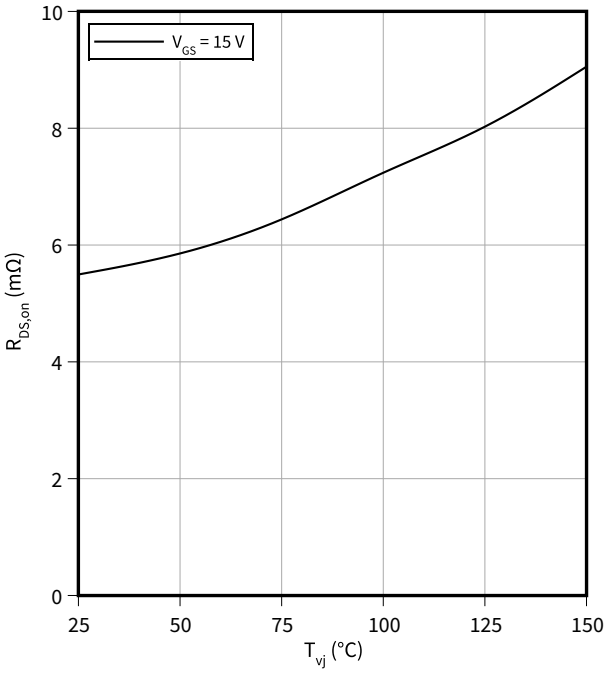
V_{DS} = 20 V



Drain-source on-resistance (typical), MOSFET

$R_{DS,on} = f(T_{vj})$

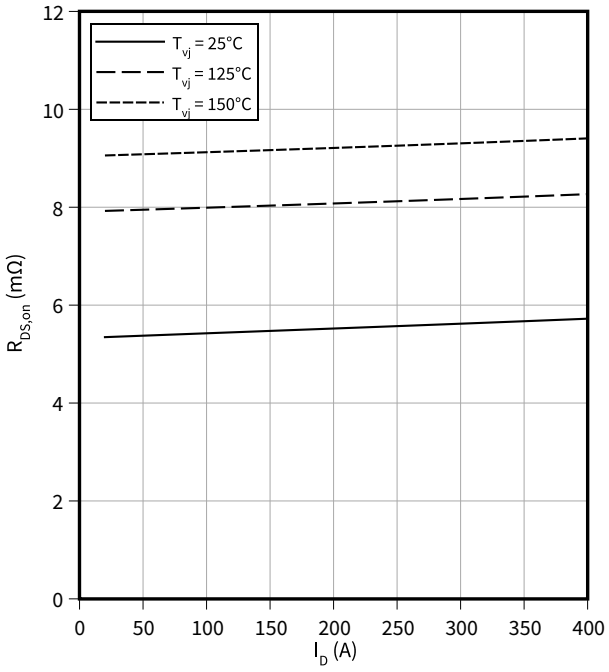
V_{GS} = 15 V



Drain-source on-resistance (typical), MOSFET

$R_{DS,on} = f(I_D)$

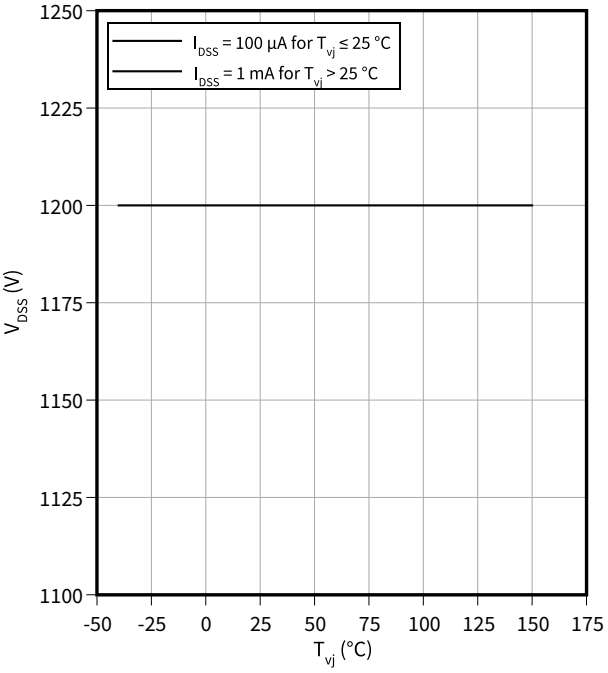
V_{GS} = 15 V



Maximum allowed drain-source voltage, MOSFET

$V_{DSS} = f(T_{vj})$

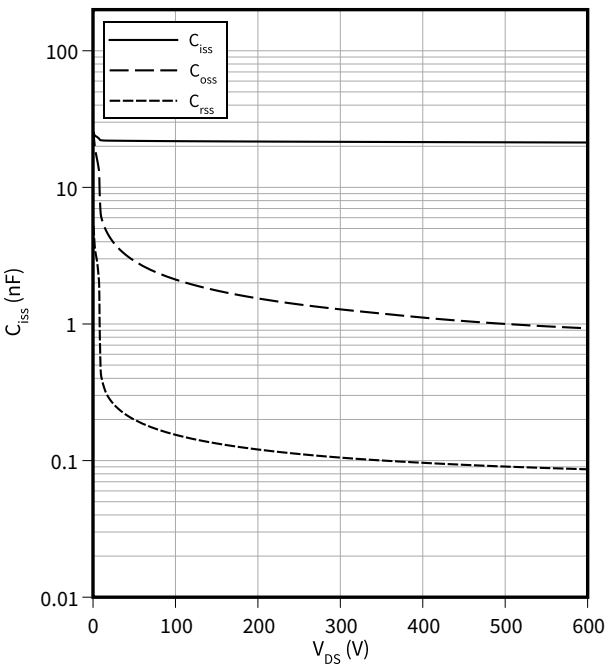
verified by characterization / design not by test



Capacity characteristic (typical), MOSFET

$C_{iss} = f(V_{DS})$, $C_{rss} = f(V_{DS})$, $C_{oss} = f(V_{DS})$

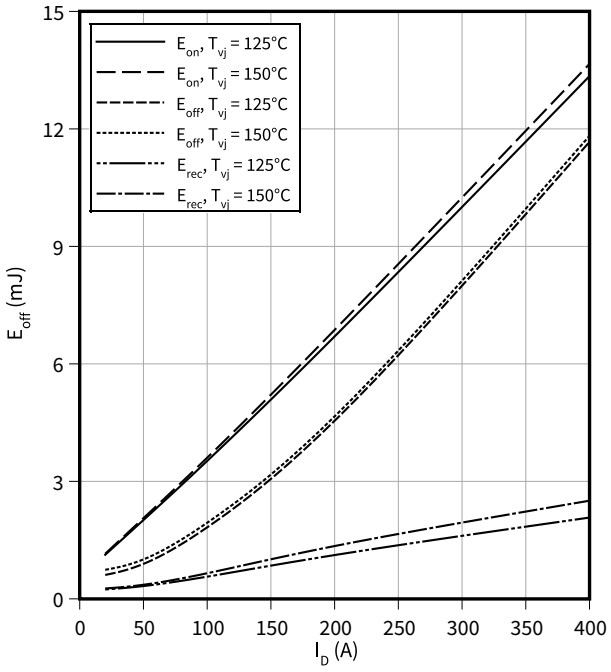
T_{vj} = 25 °C, f = 1 MHz, V_{GS} = -5/15 V



Switching losses (typical), MOSFET

$E_{off} = f(I_D)$, $E_{on} = f(I_D)$

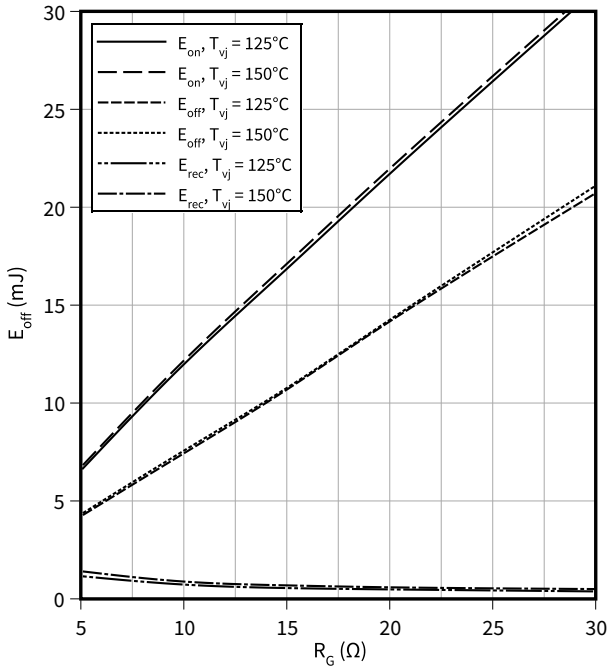
V_{DS} = 600 V, $R_{G,off}$ = 5.1 Ω, $R_{G,on}$ = 5.1 Ω, V_{GS} = ±15 V



Switching losses (typical), MOSFET

$E_{off} = f(R_G)$, $E_{on} = f(R_G)$

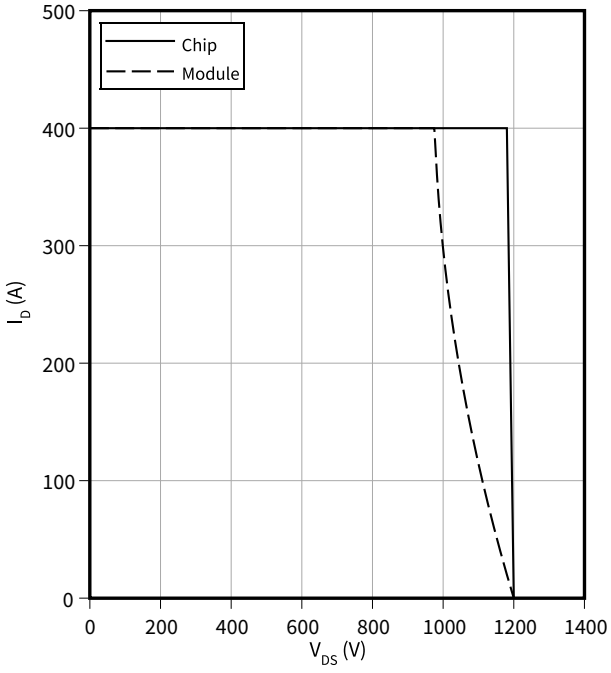
I_D = 200 A, V_{DS} = 600 V, V_{GS} = -5/15 V



Reverse bias safe operating area (RBSOA), MOSFET

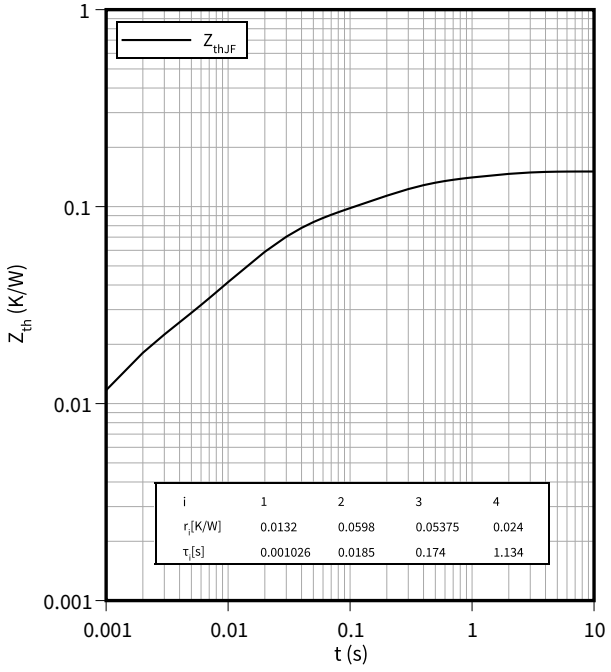
$I_D = f(V_{DS})$

V_{GS} = ±15 V, T_c = 60 °C



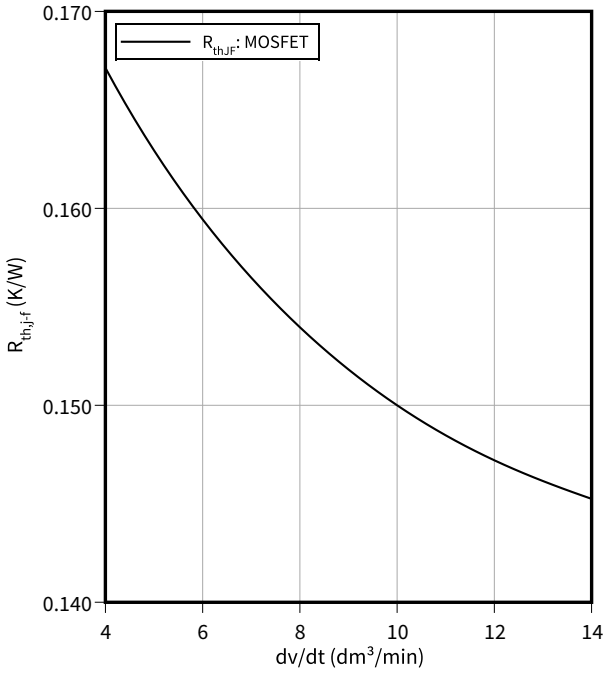
Transient thermal impedance , MOSFET

$Z_{th} = f(t)$



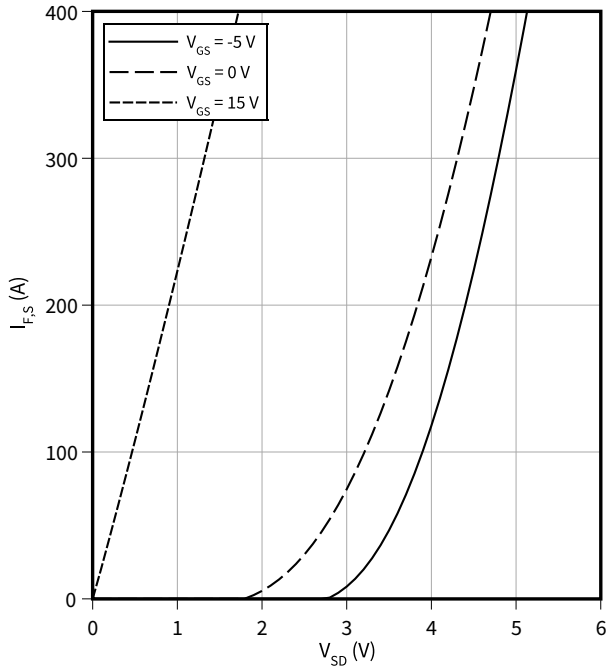
Thermal impedance , MOSFET

$R_{th,j\text{-}f} = f(dv/dt)$
fluid = 50% water/ 50% ethylenglycol , $T_f = 60$ °C



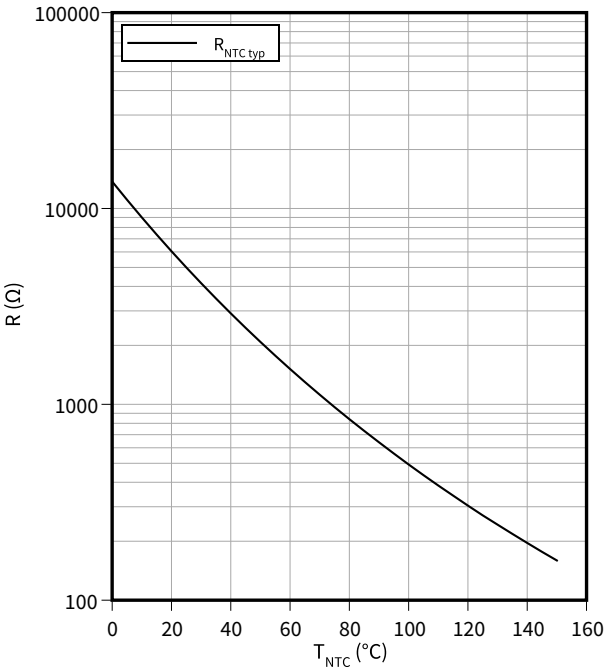
Forward characteristic body diode (typical), MOSFET

$I_{F,S} = f(V_{SD})$
$T_{vj} = 25$ °C



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



6 Circuit diagram

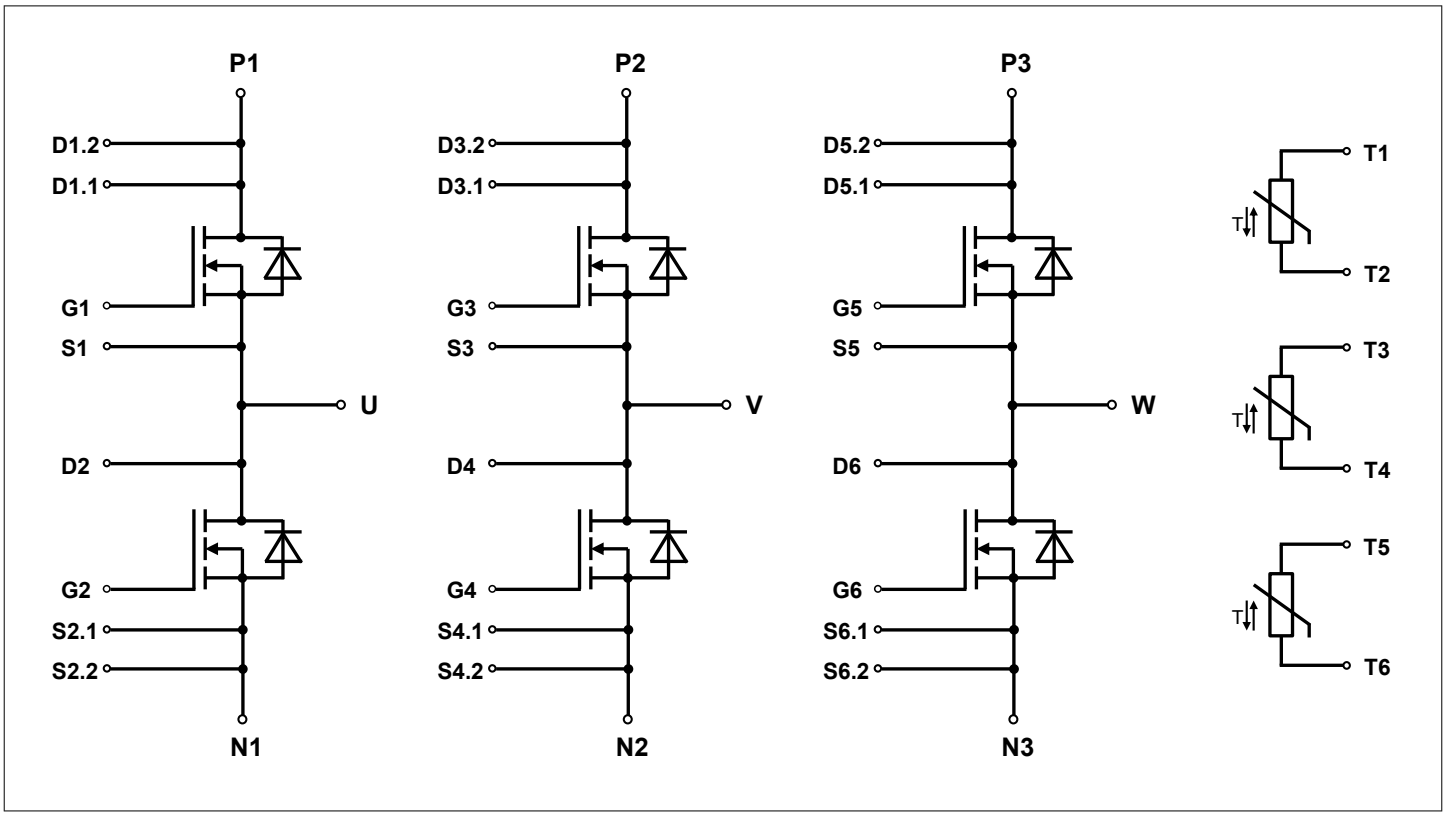


Figure 1

7 Package outlines

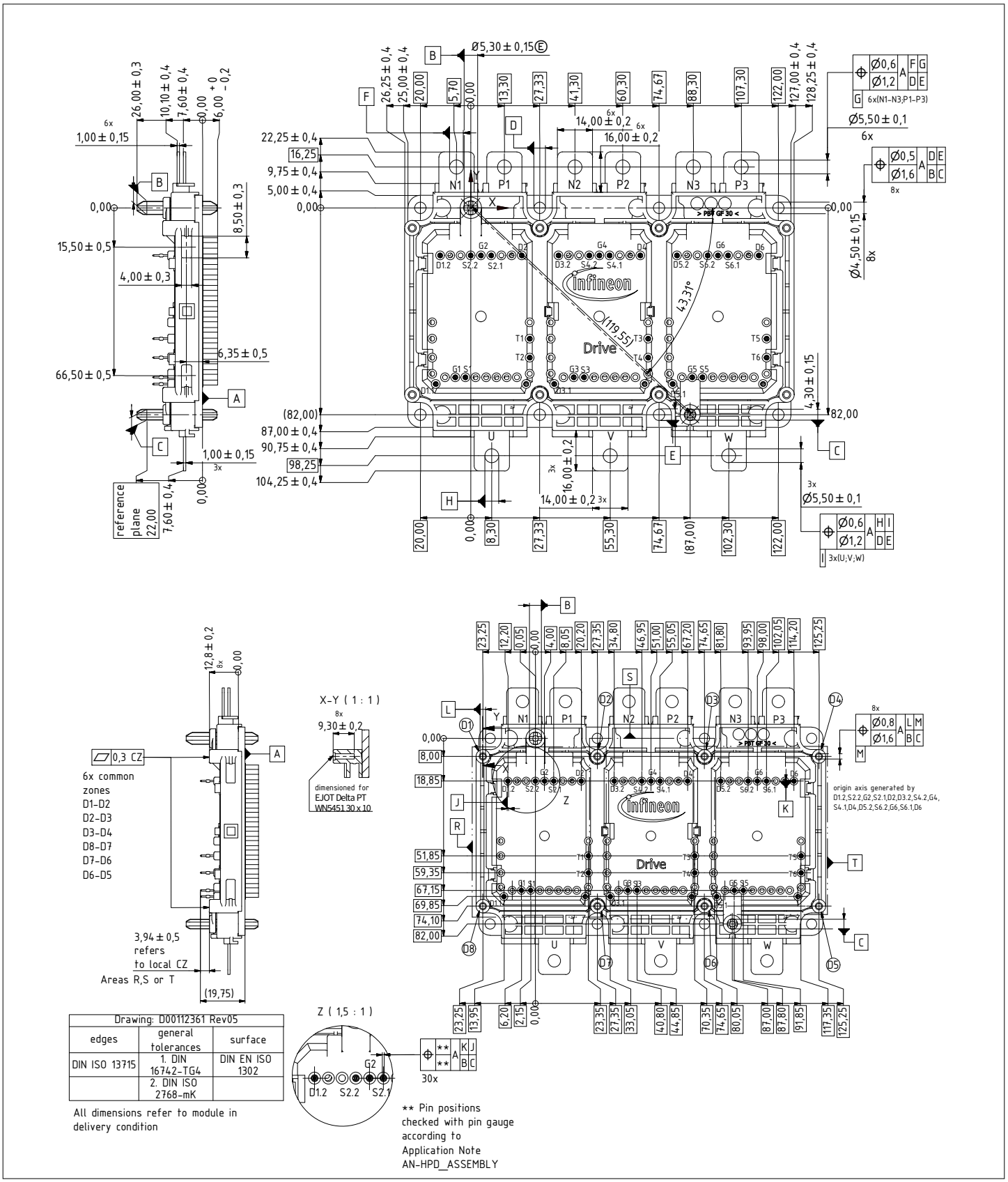


Figure 2

8 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	 71549142846550549911530	 71549142846550549911530	

Packing label code				
Code format	Barcode Code128			
Encoding	Code Set A			
Symbol size	34 digits			
Standard	IEC8859-1			
Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Identifier* X 1T S 9D Q	*Digit* 2 – 9 12 – 19 21 – 25 28 – 31 33 – 34	*Example* 95056609 2X0003E0 754389 1139 15
Example	 X950566091T2X0003E0S754389D1139Q15			

Figure 3

Revision history

Document revision	Date of release	Description of changes
V1.0	2019-09-13	Target Datasheet
V2.0	2020-04-02	Preliminary Data Sheet
V3.0	2020-06-26	
V3.1	2020-09-17	Final datasheet, correction of module weight
n/a	2020-10-05	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.10	2022-07-19	Adaption of product identification Adding electrical feature diagram Correction of typos

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